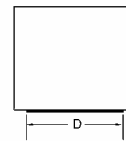
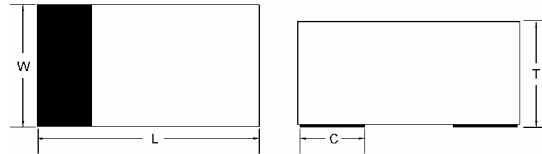


# TSS70L

## 0.07Amp Surface Mount Schottky Barrier Diode

**1005**



### Features

- ✧ Designed for mounting on small surface
- ✧ Extremely thin/leadless package
- ✧ Low capacitance
- ✧ Low forward voltage drop
- ✧ High temperature soldering:  
260°C/10 seconds at terminals
- ✧ Chip version in 1005

### Mechanical Data

- ✧ Case: 1005 Standard package, molded plastic
- ✧ Terminals: Gold plated, solderable per MIL-STD-750, method 2026.
- ✧ Polarity: Indicated by cathode band
- ✧ Mounting position: Any
- ✧ Package code: RW
- ✧ Weight: 0.006 gram (approximately)

ITEM	1005
L	0.102(2.60)
	0.095(2.40)
W	0.051(1.30)
	0.043(1.10)
T	0.035(0.90)
	0.027(0.70)
C	0.020(0.50) Typical
D	0.040(1.00) Typical

Dimensions in inches and (millimeters)

Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise specified

Type Number	Symbol	1005	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$	70	V
Reverse Voltage	$V_R$	70	V
RMS Reverse Voltage	$V_{R(RMS)}$	49	V
Average Forward Current	$I_O$	70	mA
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rate load (JEDEC method)	$I_{FSM}$	100	mA
Power Dissipation	$P_d$	200	mW
Forward Voltage $I_F=1\text{mA}$ $I_F=15\text{mA}$	$V_F$	0.41 1.0	V
Reverse Leakage Current $V_R=50\text{V}$	$I_R$	0.1	$\mu\text{A}$
Typical capacitance between terminals $V_R=0\text{V}$ , $f=1.0\text{MHz}$ reverse voltage	$C_J$	2	pF
Reverse Recovery Time ( $I_F=I_R=10\text{mA}$ , $I_{rr}=0.1 \times I_R$ , $R_L=100\Omega$ )	$T_{rr}$	5	nS
Junction Temperature	$T_J$	-65 to + 125	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-65 to + 125	$^\circ\text{C}$

RATINGS AND CHARACTERISTIC CURVES(TSS70L)

Fig. 1 - Forward characteristics

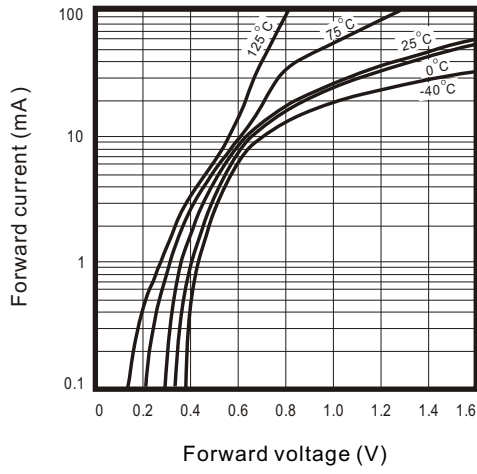


Fig. 2 - Reverse characteristics

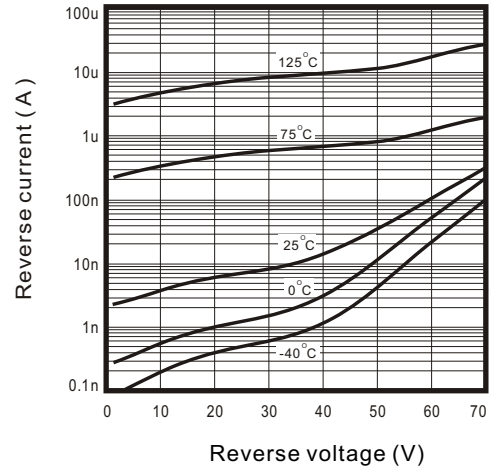


Fig.3 - Capacitance between terminals characteristics

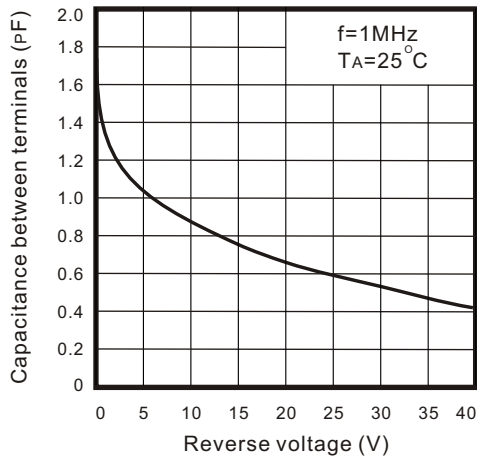


Fig.4 - Current derating curve

